



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92L Plastic-Encapsulate Transistors

KSC2328A TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 1 W ($T_{amb}=25^{\circ}C$)

Collector current

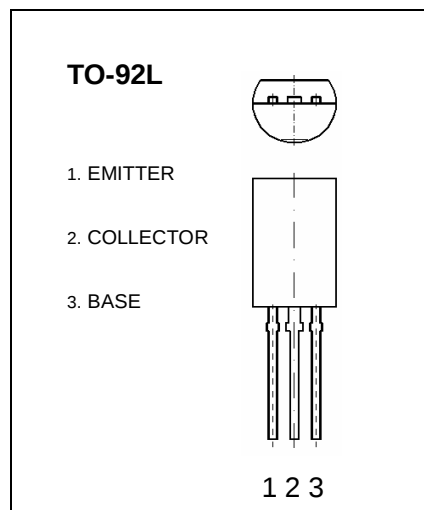
I_{CM} : 2 A

Collector-base voltage

$V_{(BR)CBO}$: 30 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	30		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{ mA}, I_B=0$	30		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{ mA}, I_C=0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{ V}, I_E=0$		0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{ V}, I_C=0$		0.1	μA
DC current gain	h_{FE}	$V_{CE}=2\text{ V}, I_C=500\text{ mA}$	100	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1.5\text{ A}, I_B=0.03\text{ A}$		2	V
Base-emitter voltage	V_{BE}	$I_C=500\text{ mA}, V_{CE}=2\text{ V}$		1	V
Transition frequency	f_T	$V_{CE}=2\text{ V}, I_C=500\text{ mA}$	80		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	100-200	160-320